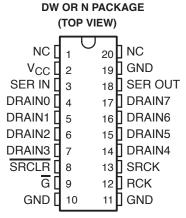
- Low $r_{DS(on)} \dots 5 \Omega$ Typical
- Avalanche Energy . . . 30 mJ
- **Eight Power DMOS-Transistor Outputs of 150-mA Continuous Current**
- 500-mA Typical Current-Limiting Capability
- Output Clamp Voltage . . . 50 V
- **Devices Are Cascadable**
- **Low Power Consumption**

description

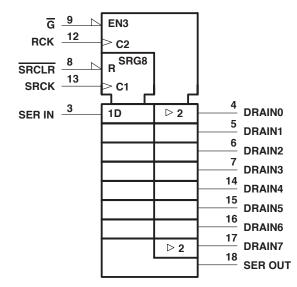
The TPIC6B595 is a monolithic, high-voltage, medium-current power 8-bit shift register designed for use in systems that require relatively high load power. The device contains a built-in voltage clamp on the outputs for inductive transient protection. Power driver applications include relays, solenoids, and other mediumcurrent or high-voltage loads.

This device contains an 8-bit serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. Data transfers through both the shift and storage registers on the rising edge of the shift-register clock (SRCK) and the register clock (RCK), respectively. The storage register transfers data to the output buffer when shiftregister clear (SRCLR) is high. When SRCLR is low, the input shift register is cleared. When output enable (\overline{G}) is held high, all data in the output buffers is held low and all drain outputs are off. When \overline{G} is held low, data from the storage register is transparent to the output buffers. When data in the output buffers is low, the DMOS-transistor outputs are off. When data is high, the DMOStransistor outputs have sink-current capability. The serial output (SER OUT) allows for cascading of the data from the shift register to additional devices.



NC - No internal connection

logic symbol[†]

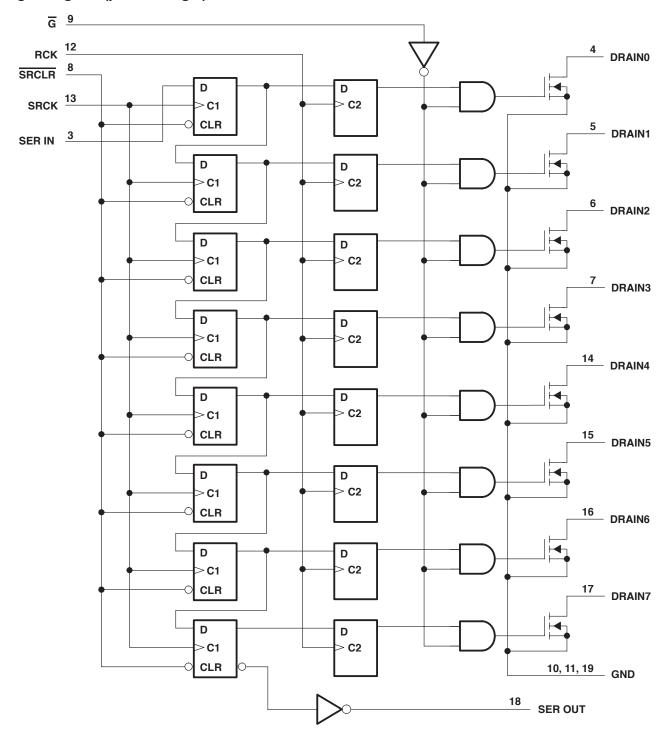


† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

Outputs are low-side, open-drain DMOS transistors with output ratings of 50 V and 150-mA continuous sinkcurrent capability. Each output provides a 500-mA typical current limit at $T_C = 25^{\circ}$ C. The current limit decreases as the junction temperature increases for additional device protection.

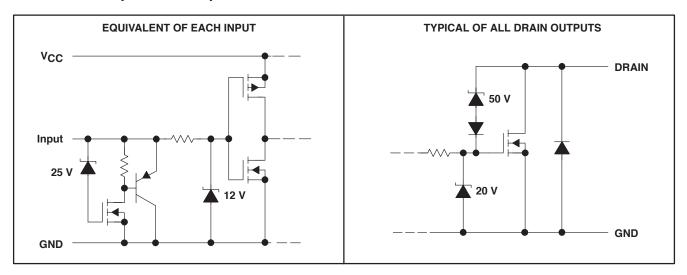
The TPIC6B595 is characterized for operation over the operating case temperature range of -40°C to 125°C.

logic diagram (positive logic)





schematic of inputs and outputs



absolute maximum ratings over recommended operating case temperature range (unless otherwise noted) \dagger

| Logic supply voltage, V _{CC} (see Note 1) | 7 V |
|--|------------------------------|
| Logic input voltage range, V ₁ | 0.3 V to 7 V |
| Power DMOS drain-to-source voltage, V _{DS} (see Note 2) | 50 V |
| Continuous source-to-drain diode anode current | |
| Pulsed source-to-drain diode anode current (see Note 3) | 1 A |
| Pulsed drain current, each output, all outputs on, I _D , T _C = 25°C (see Note 3) | 500 mA |
| Continuous drain current, each output, all outputs on, I _D , T _C = 25°C | 150 mA |
| Peak drain current single output, I _{DM} ,T _C = 25°C (see Note 3) | 500 mA |
| Single-pulse avalanche energy, E _{AS} (see Figure 4) | 30 mJ |
| Avalanche current, I _{AS} (see Note 4) | 500 mA |
| Continuous total dissipation | See Dissipation Rating Table |
| Operating virtual junction temperature range, T _{.J.} | |
| Operating case temperature range, T _C | 40°C to 125°C |
| Storage temperature range | |
| Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds | 260°C |

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values are with respect to GND.
 - 2. Each power DMOS source is internally connected to GND.
 - 3. Pulse duration \leq 100 μ s and duty cycle \leq 2%.
 - 4. DRAIN supply voltage = 15 V, starting junction temperature (T_{JS}) = 25°C, L = 200 mH, I_{AS} = 0.5 A (see Figure 4).

DISSIPATION RATING TABLE

| PACKAGE | $T_C \le 25^{\circ}C$ POWER RATING | DERATING FACTOR ABOVE T _C = 25°C | T _C = 125°C POWER RATING | |
|---------|------------------------------------|--|--|--|
| DW | 1389 mW | 11.1 mW/°C | 278 mW | |
| N | 1050 mW | 10.5 mW/°C | 263 mW | |



TPIC6B595 POWER LOGIC 8-BIT SHIFT REGISTER

SLIS032A - JULY 1995 - REVISED MAY 2005

recommended operating conditions

| | MIN | MAX | UNIT |
|---|----------------------|----------------------|------|
| Logic supply voltage, V _{CC} | 4.5 | 5.5 | V |
| High-level input voltage, V _{IH} | 0.85 V _{CC} | | V |
| Low-level input voltage, V _{IL} | | 0.15 V _{CC} | V |
| Pulsed drain output current, T _C = 25°C, V _{CC} = 5 V (see Notes 3 and 5) | -500 | 500 | mA |
| Setup time, SER IN high before SRCK↑, t _{SU} (see Figure 2) | 20 | | ns |
| Hold time, SER IN high after SRCK↑, th (see Figure 2) | 20 | | ns |
| Pulse duration, t _W (see Figure 2) | 40 | | ns |
| Operating case temperature, T _C | -40 | 125 | °C |

electrical characteristics, $V_{CC} = 5 \text{ V}$, $T_{C} = 25^{\circ}\text{C}$ (unless otherwise noted)

| | PARAMETER | TEST CONI | DITIONS | MIN | TYP | MAX | UNIT |
|----------------------|---|---|---------------------------------------|-----|-------|-----|------|
| V _{(BR)DSX} | Drain-to-source breakdown voltage | I _D = 1 mA | | 50 | | | V |
| V _{SD} | Source-to-drain diode forward voltage | I _F = 100 mA | | | 0.85 | 1 | ٧ |
| V | High-level output voltage, | $I_{OH} = -20 \mu A$, $V_{CC} = 4.5 V$ | ' | 4.4 | 4.49 | | V |
| VOH | SER OUT | $I_{OH} = -4 \text{ mA}, V_{CC} = 4.5 \text{ V}$ | 1 | 4 | 4.2 | | V |
| V = . | Low-level output voltage, | $I_{OL} = 20 \mu A$, $V_{CC} = 4.5 V$ | 1 | | 0.005 | 0.1 | V |
| VOL | SER OUT | $I_{OL} = 4 \text{ mA}, V_{CC} = 4.5 \text{ V}$ | 1 | | 0.3 | 0.5 | ٧ |
| lіН | High-level input current | $V_{CC} = 5.5 \text{ V}, V_I = V_{CC}$ | | | | 1 | μΑ |
| I _I L | Low-level input current | $V_{CC} = 5.5 \text{ V}, V_{I} = 0$ | | | | -1 | μΑ |
| | | V 55V | All outputs off | | 20 | 100 | • |
| lcc | Logic supply current | V _{CC} = 5.5 V | All outputs on | | 150 | 300 | μΑ |
| ICC(FRQ) | Logic supply current at frequency | f _{SRCK} = 5 MHzC _L = 30 pF, All outputs off, | See Figures 2 and 6 | | 0.4 | 5 | mA |
| I _N | Nominal current | $V_{DS(on)} = 0.5 \text{ V},$ $I_{N} = I_{D},$ $T_{C} = 85^{\circ}C$ | See Notes 5, 6, and 7 | | 90 | | mA |
| | Off-state drain current | $V_{DS} = 40 \text{ V}, V_{CC} = 5.5 \text{ V}$ | 1 | | 0.1 | 5 | A |
| IDSX | On-state drain current | $V_{DS} = 40 \text{ V}, V_{CC} = 5.5 \text{ V}$ | ′, T _C = 125°C | | 0.15 | 8 | μΑ |
| | | $I_D = 100 \text{ mA}, V_{CC} = 4.5 \text{ V}$ | ' | | 4.2 | 5.7 | |
| r _{DS(on)} | Static drain-source on-state resistance | $I_D = 100 \text{ mA}, T_C = 125^{\circ}\text{C}, \\ V_{CC} = 4.5 \text{ V}$ | See Notes 5 and 6 and Figures 7 and 8 | | 6.8 | 9.5 | Ω |
| | | $I_D = 350 \text{ mA}, V_{CC} = 4.5 \text{ V}$ | ′ | | 5.5 | 8 | |

NOTES: 3. Pulse duration \leq 100 μ s and duty cycle \leq 2%.

- 5. Technique should limit $T_J T_C$ to 10°C maximum.
- 6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.
- 7. Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at T_C = 85°C.



switching characteristics, $V_{CC} = 5 \text{ V}$, $T_{C} = 25^{\circ}\text{C}$

| | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-----------------|--|---|-----|-----|-----|------|
| tPLH | Propagation delay time, low-to-high-level output from \overline{G} | | | 150 | | ns |
| tPHL | Propagation delay time, high-to-low-level output from \overline{G} | $C_L = 30 \text{ pF}, \qquad I_D = 100 \text{ mA},$ | | 90 | | ns |
| t _r | Rise time, drain output | See Figures 1, 2, and 9 | | 200 | | ns |
| t _f | Fall time, drain output | | | 200 | | ns |
| ta | Reverse-recovery-current rise time | $I_F = 100 \text{ mA}, \qquad \text{di/dt} = 20 \text{ A/}\mu\text{s},$ | | 100 | | |
| t _{rr} | Reverse-recovery time | See Notes 5 and 6 and Figure 3 | | 300 | | ns |

NOTES: 5. Technique should limit $T_J - T_C$ to 10°C maximum.

thermal resistance

| PARAMETER | | | TEST CONDITIONS | MIN | MAX | UNIT |
|-----------------|---|------------|--------------------------------|-----|-----|-------|
| D | Thermal registeres in patien to embient | DW package | All Q outputs with agual power | | 90 | °C/W |
| $R_{\theta JA}$ | Thermal resistance, junction-to-ambient | N package | All 8 outputs with equal power | | 95 | -0/00 |

PARAMETER MEASUREMENT INFORMATION 5 V 24 V ID. **VCC** SRCLR 5 V G $R_L = 235 \Omega$ 13 0 V **SRCK** 4-7, DUT 5 V Output **SER IN** 14-17 Word 3 0 V **DRAIN SER IN** Generator (see Note A) 12 $C_L = 30 pF$ RCK 0 V (see Note B) 9 5 V G SRCLR **GND** 24 V 10, 11, 19 DRAIN1 0.5 V **VOLTAGE WAVEFORMS TEST CIRCUIT**

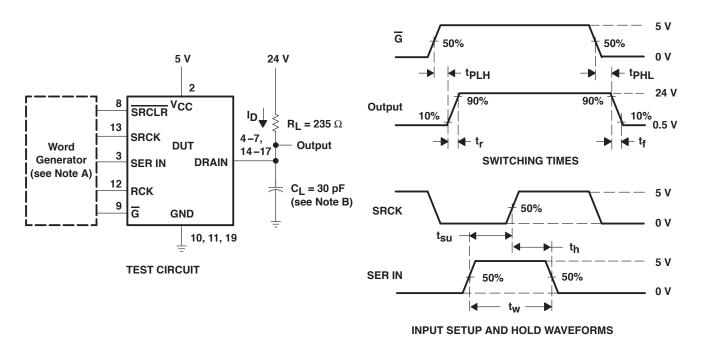
NOTES: A. The word generator has the following characteristics: $t_f \le 10$ ns, $t_f \le 10$ ns, $t_W = 300$ ns, pulsed repetition rate (PRR) = 5 kHz, $Z_O = 50 \ \Omega$.

B. C_L includes probe and jig capacitance.

Figure 1. Resistive-Load Test Circuit and Voltage Waveforms

^{6.} These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

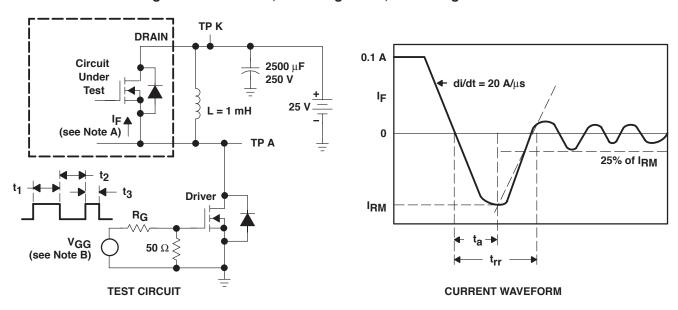
PARAMETER MEASUREMENT INFORMATION



NOTES: A. The word generator has the following characteristics: $t_{\Gamma} \le 10$ ns, $t_{W} = 300$ ns, pulsed repetition rate (PRR) = 5 kHz, $Z_{O} = 50~\Omega$.

B. C_L includes probe and jig capacitance.

Figure 2. Test Circuit, Switching Times, and Voltage Waveforms



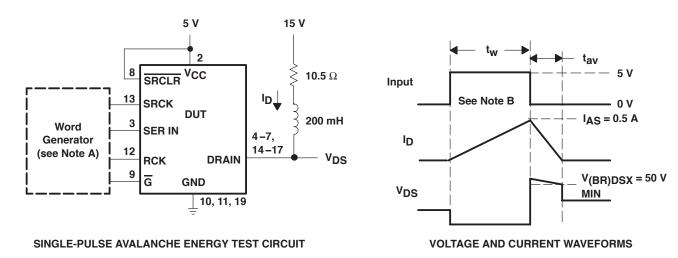
NOTES: A. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.

B. The V_{GG} amplitude and R_{G} are adjusted for di/dt = 20 A/ μ s. A V_{GG} double-pulse train is used to set I_{F} = 0.1 A, where t_{1} = 10 μ s, t_{2} = 7 μ s, and t_{3} = 3 μ s.

Figure 3. Reverse-Recovery-Current Test Circuit and Waveforms of Source-to-Drain Diode



PARAMETER MEASUREMENT INFORMATION

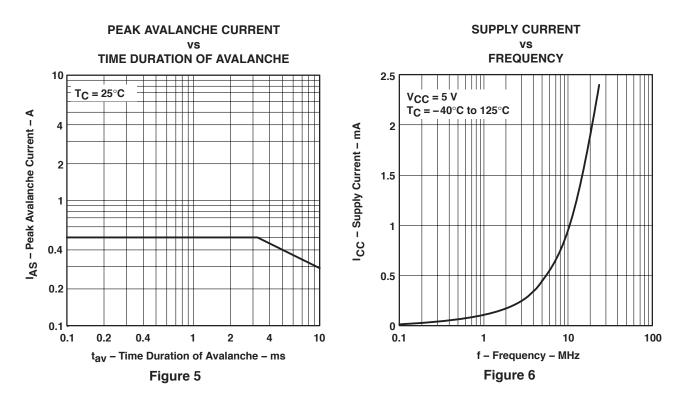


NOTES: A. The word generator has the following characteristics: $t_f \le 10$ ns, $t_f \le 10$ ns, $Z_O = 50 \Omega$.

B. Input pulse duration, t_W , is increased until peak current $I_{AS} = 0.5 \text{ A}$. Energy test level is defined as $E_{AS} = I_{AS} \times V_{(BR)DSX} \times t_{aV}/2 = 30 \text{ mJ}$.

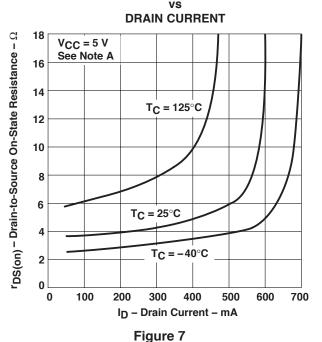
Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

DRAIN-TO-SOURCE ON-STATE RESISTANCE



STATIC DRAIN-TO-SOURCE ON-STATE RESISTANCE

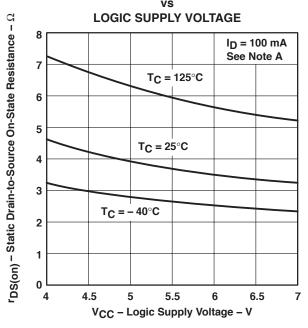


Figure 8

SWITCHING TIME vs

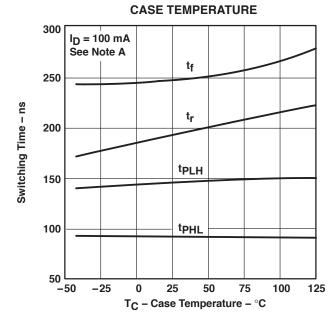
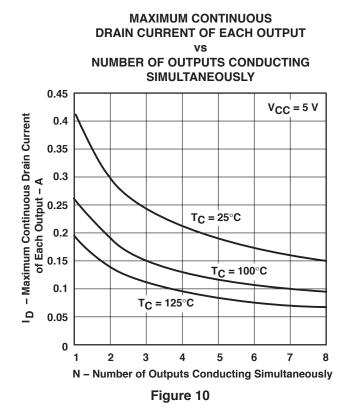


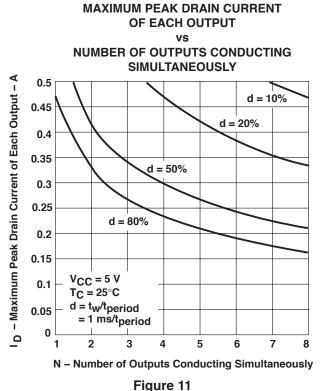
Figure 9

NOTE C: Technique should limit $T_J - T_C$ to 10°C maximum.



THERMAL INFORMATION





Revision History

| DATE | REV | PAGE | SECTION | DESCRIPTION |
|---------|-----|------|----------|------------------------------|
| 5/18/05 | Α | 5 | Figure 1 | Changed SRCLR timing diagram |
| 7/1995 | * | | | Original reversion |

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.



PACKAGE OPTION ADDENDUM

2-Mar-2006

PACKAGING INFORMATION

| Orderable Device | Status ⁽¹⁾ | Package Type | Package Drawing | Pins | Package Qty | Eco Plan ⁽²⁾ | Lead/Ball Finish | MSL Peak Temp ⁽³⁾ |
|------------------|-----------------------|-----------------|--------------------|------|----------------|-------------------------|------------------|------------------------------|
| TPIC6B595DW | ACTIVE | SOIC | DW | 20 | 25 | TBD | CU NIPDAU | Level-1-220C-UNLIM |
| TPIC6B595DWG4 | ACTIVE | SOIC | DW | 20 | 25 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM |
| TPIC6B595DWR | ACTIVE | SOIC | DW | 20 | 2000 | TBD | CU NIPDAU | Level-1-220C-UNLIM |
| TPIC6B595N | ACTIVE | PDIP | N | 20 | 20 | Pb-Free (RoHS) | CU NIPDAU | N / A for Pkg Type |

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



DW (R-PDSO-G20)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AC.



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Mailing Address: Texas Instruments

Post Office Box 655303 Dallas, Texas 75265

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